

FIG. 1

FIG. 3A

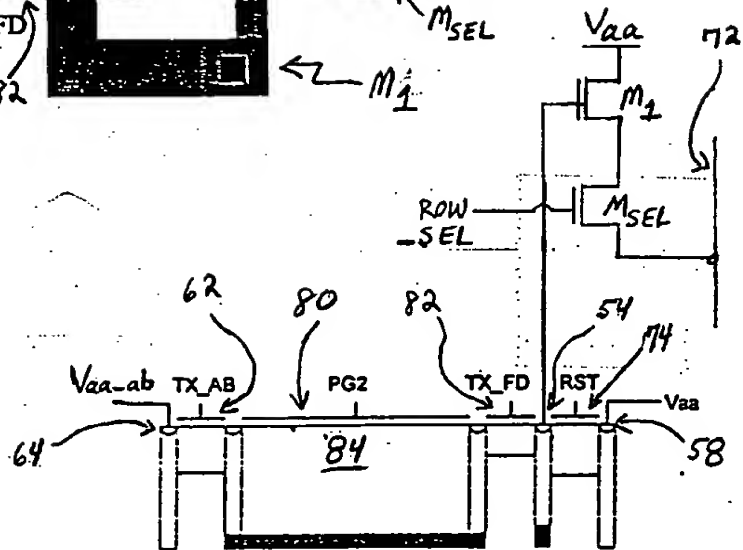


FIG. 3B

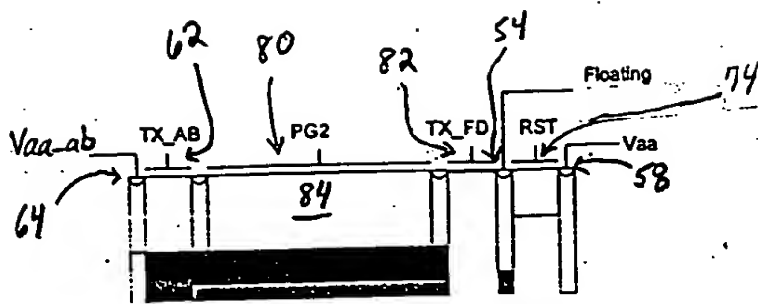


FIG. 4A

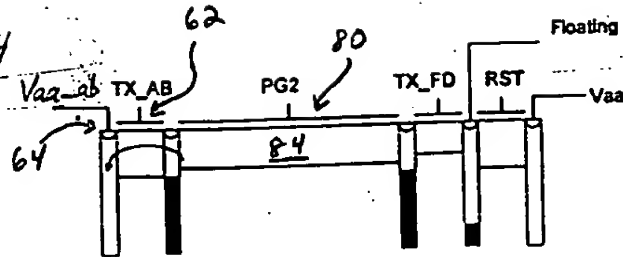
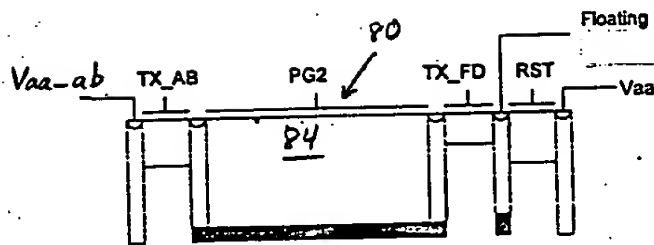


FIG. 4B



$Q_{rem}(TX-AB)$ FIG. 4C

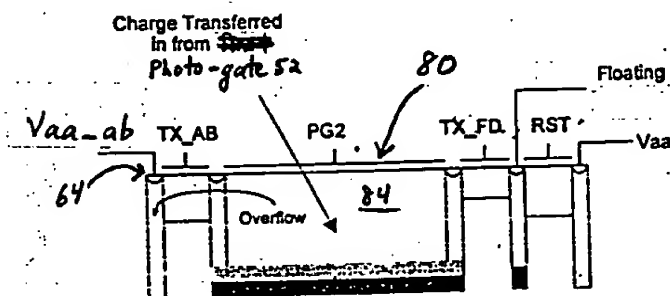


FIG. 4D

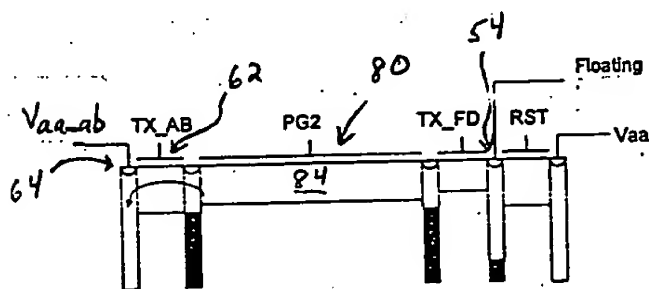
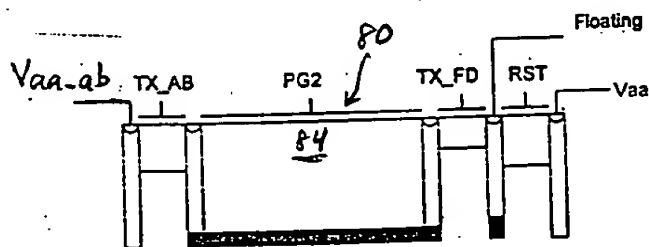


FIG. 4E



$Q_{rem}(TX-AB)$ FIG. 4F

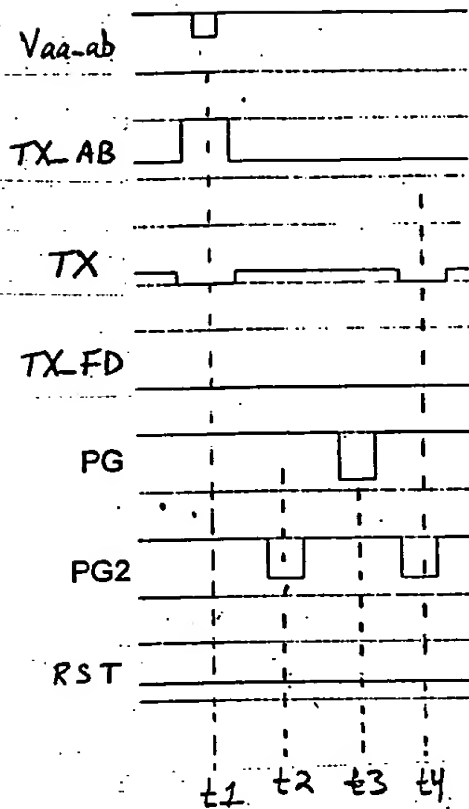


FIG. 5

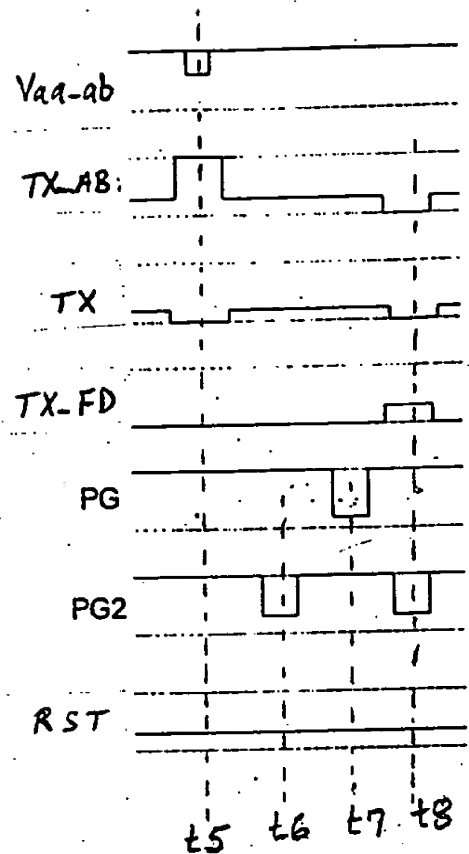


FIG. 7

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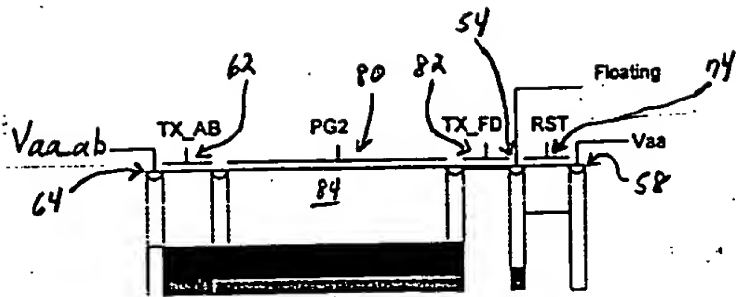


FIG. 6A

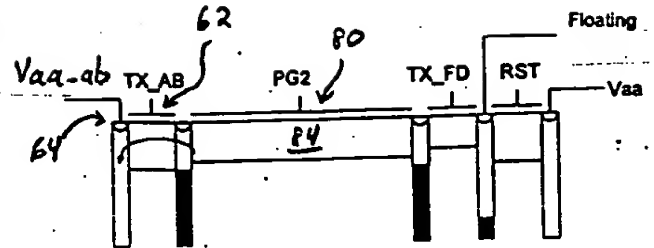


FIG. 6B

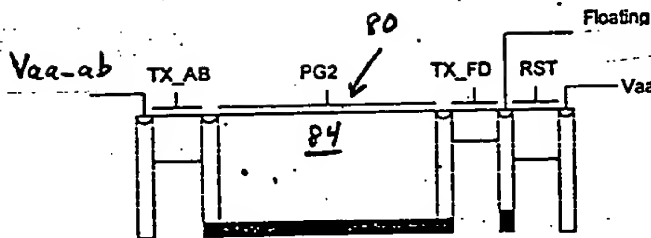


FIG. 6C
 $Q_{rem}(TX-AB)$

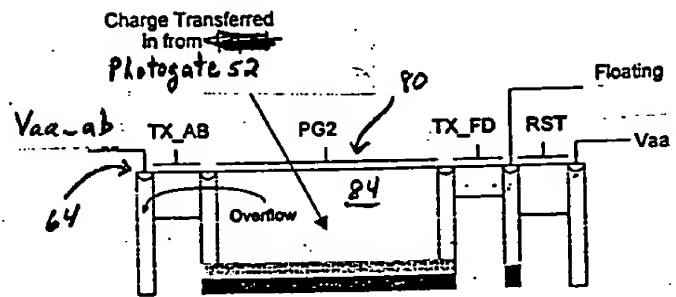


FIG. 6D

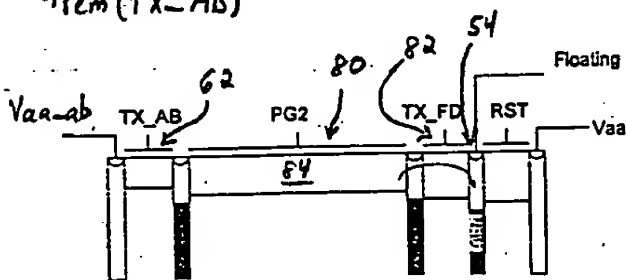


FIG. 6E

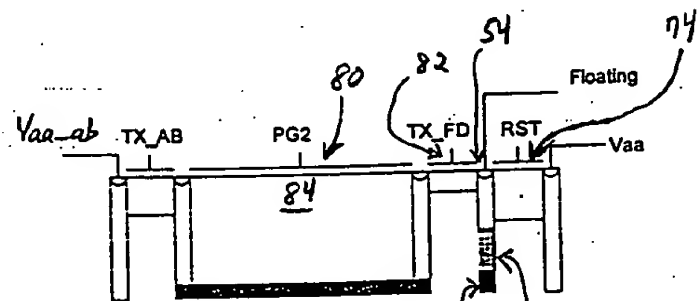


FIG. 6F
 $Q_{rem}(TX-FD)$
 Q_{sig}
 Q_{err}

FIG. 8A

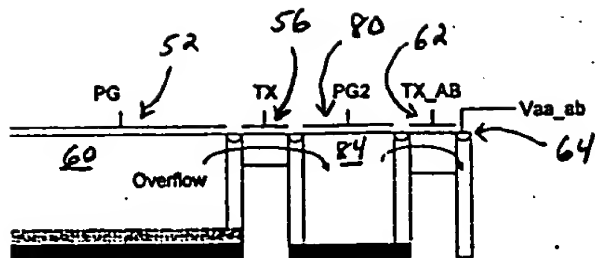


FIG. 8B

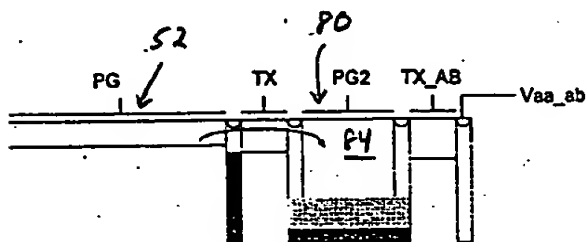
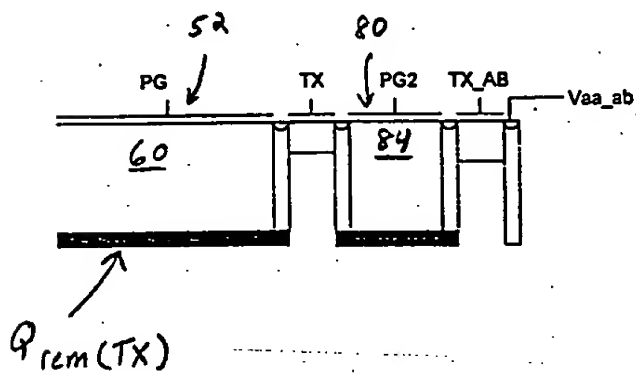


FIG. 8C



A cross-sectional view of a semiconductor device. A central horizontal layer is labeled **PG2** and **PG4**. Above this layer, from left to right, are regions labeled **TX_AB**, **TX_FD**, and **RST**. A line labeled **Vaa-ab** points to the left side of the **TX_AB** region. A line labeled **Vaa** points to the right side of the **RST** region. A line labeled **80** points to the **PG2** layer. A line labeled **64** points to the leftmost vertical structure. A line labeled **Floating** points to the top surface of the **PG2** layer.

$$Q_{rem}(TX-AB)$$

FIG. 9D

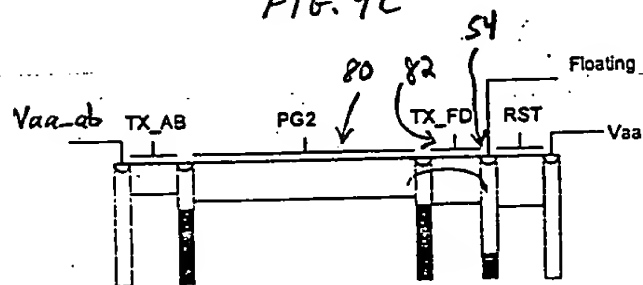


FIG. 9E

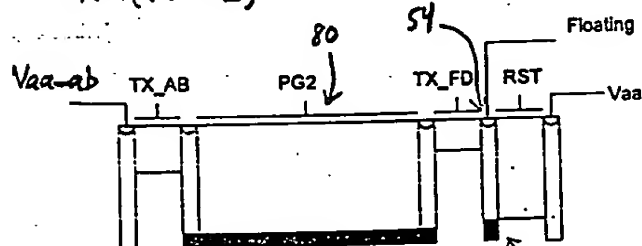


FIG. 9F

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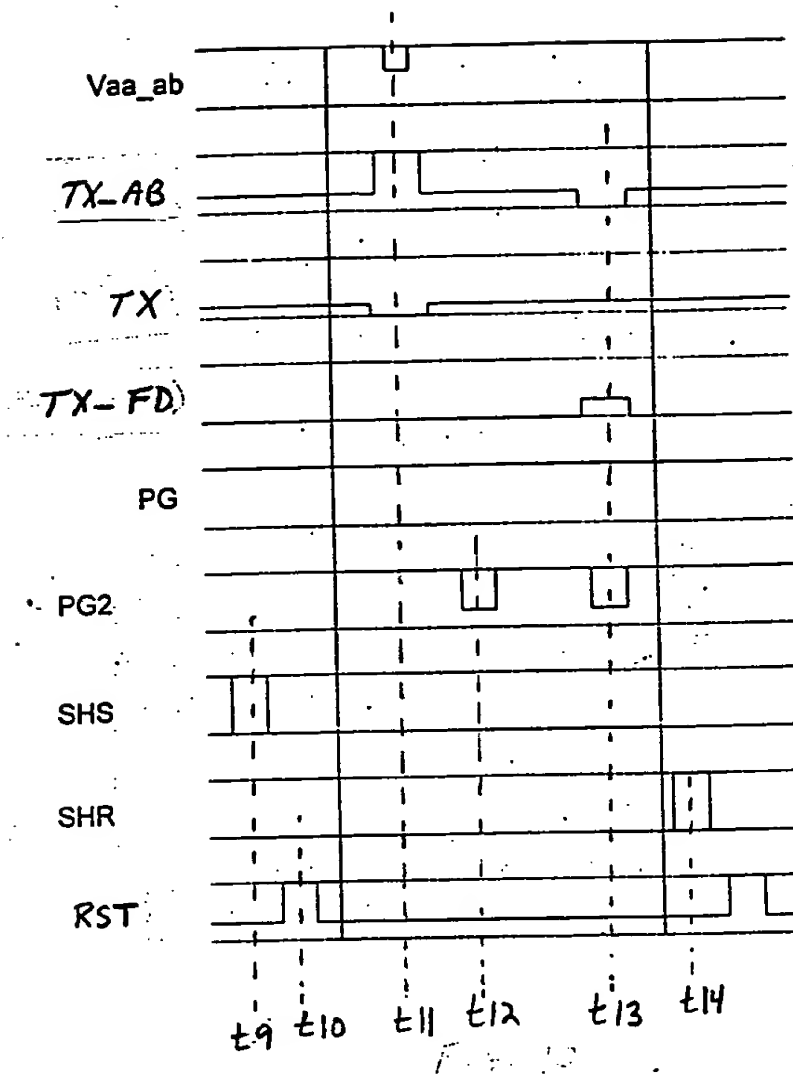


FIG. 10

FIG. 11